

MOSFET - Power, Single N-Channel, Source Down DualCool 33, WDFN9

80 V, 3.6 mΩ, 107 A

NTTFSSCH4D0N08XL

Features

- Excellent Thermal Conduction by Advanced Source-Down Center Gate Dual-Cooling Package Technology (3.3x3.3mm)
- Ultra Low $R_{DS(on)}$ to Improve System Efficiency
- Low Q_G and Capacitance to Minimize Driving and Switching Losses
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

Applications

- High Switching Frequency DC-DC Conversion
- Synchronous Rectifier

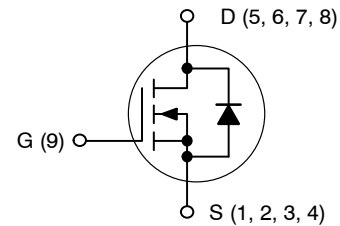
MAXIMUM RATINGS ($T_J = 25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-to-Source Voltage	V_{DS}	80	V
Gate-to-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current (Note 1)	I_D	$T_C = 25^\circ\text{C}$	A
		$T_C = 100^\circ\text{C}$	
Power Dissipation (Notes 1, 2)	P_D	102	W
Pulsed Drain Current	I_{DM}	$T_C = 25^\circ\text{C}$, $t_p = 100 \mu\text{s}$	A
Pulsed Source Current (Body Diode)		I_{SM}	
Operating Junction and Storage Temperature Range	T_J, T_{stg}	-55 to $+175$	$^\circ\text{C}$
Source Current (Body Diode)	I_S	155	A
Single Pulse Avalanche Energy ($I_{PK} = 40 \text{ A}$)	E_{AS}	80	mJ
Lead Temperature for Soldering Purposes (1/8" from case for 10 s)	T_L	260	$^\circ\text{C}$

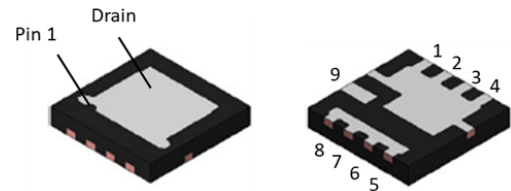
Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. The entire application environment impacts the thermal resistance values shown, they are not constants and are valid for the particular conditions noted.
2. Surface-mounted on FR4 board using a 1 in² pad size, 1 oz Cu pad.
3. E_{AS} of 80 mJ is based on started $T_J = 25^\circ\text{C}$, $I_{AS} = 40 \text{ A}$, $V_{GS} = 10 \text{ V}$, 100% avalanche tested.

$V_{(BR)DS}$	$R_{DS(ON)} \text{ MAX}$	$I_D \text{ MAX}$
80 V	3.6 mΩ @ 10 V	107 A
	5.3 mΩ @ 4.5 V	

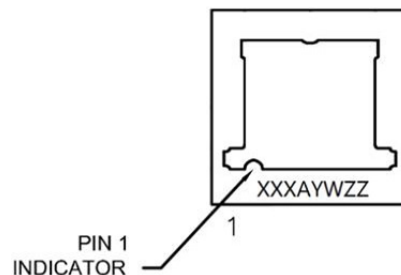


N-CHANNEL MOSFET



WDFN9
CASE 511BX

MARKING DIAGRAM



4D0 = Specific Device Code
A = Assembly Location
YW = Assembly Start Week
ZZ = Assembly Lot Number

ORDERING INFORMATION

See detailed ordering and shipping information on page 6 of this data sheet.

NTTFSSCH4D0N08XL

THERMAL CHARACTERISTICS

Parameter	Symbol	Max	Unit
Thermal Resistance, Junction-to-Case (Bottom)	$R_{\theta JCB}$	1.5	°C/W
Thermal Resistance, Junction-to-Case (Top)	$R_{\theta JCT}$	1.2	
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	60	

ELECTRICAL CHARACTERISTICS ($T_J = 25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
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OFF CHARACTERISTICS

Drain-to-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0\text{ V}, I_D = 1\text{ mA}, T_J = 25^\circ\text{C}$	80			V
Drain-to-Source Breakdown Voltage Temperature Coefficient	$\Delta V_{(BR)DSS} / \Delta T_J$	$I_D = 1\text{ mA}$, Referenced to 25°C		32		mV/°C
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 80\text{ V}, T_J = 25^\circ\text{C}$			10	μA
		$V_{DS} = 80\text{ V}, T_J = 125^\circ\text{C}$			250	
Gate-to-Source Leakage Current	I_{GSS}	$V_{DS} = 0\text{ V}, V_{GS} = 20\text{ V}$			100	nA

ON CHARACTERISTICS

Drain-to-Source On Resistance	$R_{DS(ON)}$	$V_{GS} = 10\text{ V}, I_D = 23\text{ A}$		3.1	3.6	m Ω
		$V_{GS} = 4.5\text{ V}, I_D = 18\text{ A}$		3.9	5.3	
Gate Threshold Voltage	$V_{GS(TH)}$	$V_{GS} = V_{DS}, I_D = 115\text{ }\mu\text{A}, T_J = 25^\circ\text{C}$	1.5		2.1	V
Gate Threshold Voltage Temperature Coefficient	$\Delta V_{GS(TH)} / \Delta T_J$	$V_{GS} = V_{DS}, I_D = 115\text{ }\mu\text{A}$		-6		mV/°C
Forward Transconductance	g_{FS}	$V_{DS} = 5\text{ V}, I_D = 23\text{ A}$		156		S

CHARGES, CAPACITANCES & GATE RESISTANCE

Input Capacitance	C_{ISS}	$V_{GS} = 0\text{ V}, V_{DS} = 40\text{ V}, f = 1\text{ MHz}$		2520		pF
Output Capacitance	C_{OSS}			630		
Reverse Transfer Capacitance	C_{RSS}			18		
Output Charge	Q_{OSS}			47		nC
Total Gate Charge	$Q_{G(TOT)}$	$V_{GS} = 4.5\text{ V}, V_{DD} = 40\text{ V}; I_D = 23\text{ A}$		19		
				40		
Threshold Gate Charge	$Q_{G(TH)}$	$V_{GS} = 10\text{ V}, V_{DD} = 40\text{ V}; I_D = 23\text{ A}$		4.6		
Gate-to-Source Charge	Q_{GS}			8.1		
Gate-to-Drain Charge	Q_{GD}			6.2		
Gate Plateau Voltage	V_{GP}			3.1		V
Gate Resistance	R_G	$f = 1\text{ MHz}$		0.4		Ω

SWITCHING CHARACTERISTICS

Turn-On Delay Time	$t_{d(ON)}$	Resistive Load, $V_{GS} = 0/10\text{ V}, V_{DD} = 40\text{ V},$ $I_D = 23\text{ A}, R_G = 2.5\text{ }\Omega$		11		ns
Rise Time	t_r			5		
Turn-Off Delay Time	$t_{d(OFF)}$			28		
Fall Time	t_f			4		

SOURCE-TO-DRAIN DIODE CHARACTERISTICS

Forward Diode Voltage	V_{SD}	$V_{GS} = 0\text{ V}, I_S = 23\text{ A}, T_J = 25^\circ\text{C}$		0.8		V
		$V_{GS} = 0\text{ V}, I_S = 23\text{ A}, T_J = 125^\circ\text{C}$		0.7		

NTTFSSCH4D0N08XL

ELECTRICAL CHARACTERISTICS (T_J = 25°C unless otherwise specified)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
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SOURCE-TO-DRAIN DIODE CHARACTERISTICS

Reverse Recovery Time	t _{RR}	V _{GS} = 0 V, I _S = 23 A, dI/dt = 1000 A/μs, V _{DD} = 40 V		19		ns
Charge Time	t _a			11		
Discharge Time	t _b			8		
Reverse Recovery Charge	Q _{RR}			109		nC

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

TYPICAL CHARACTERISTICS

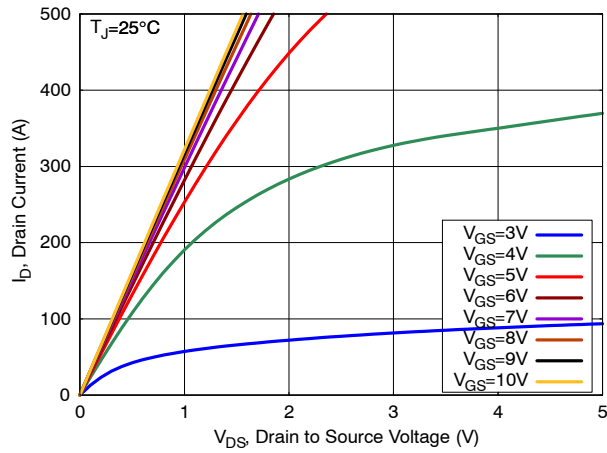


Figure 1. On-Region Characteristics

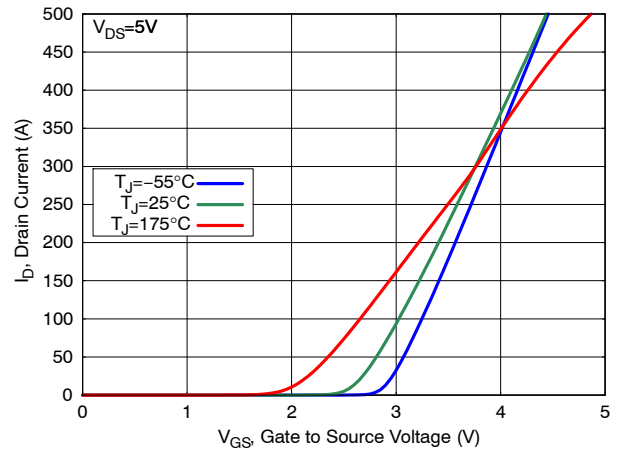


Figure 2. Transfer Characteristics

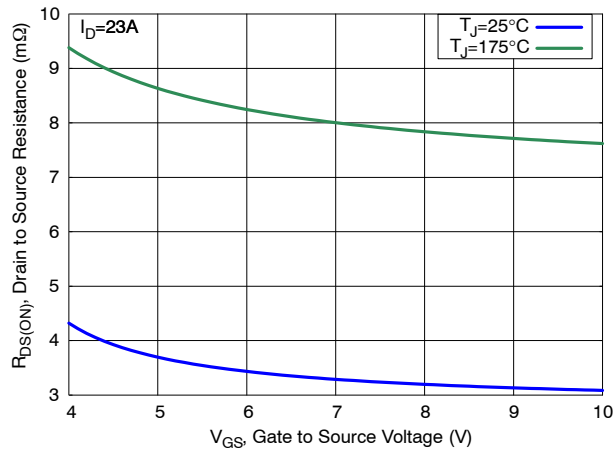


Figure 3. On-Resistance vs. Gate Voltage

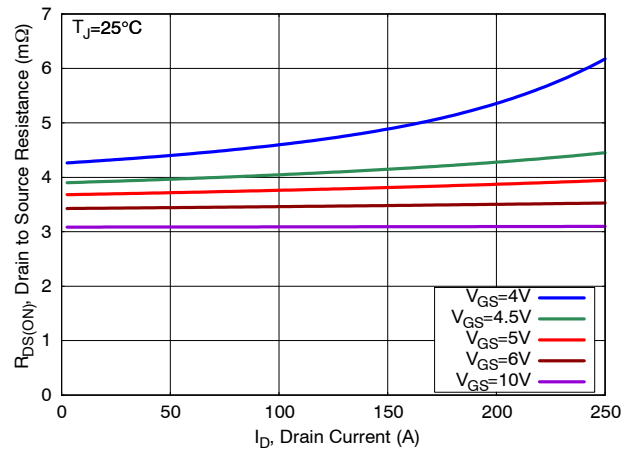


Figure 4. On-Resistance vs. Drain Current

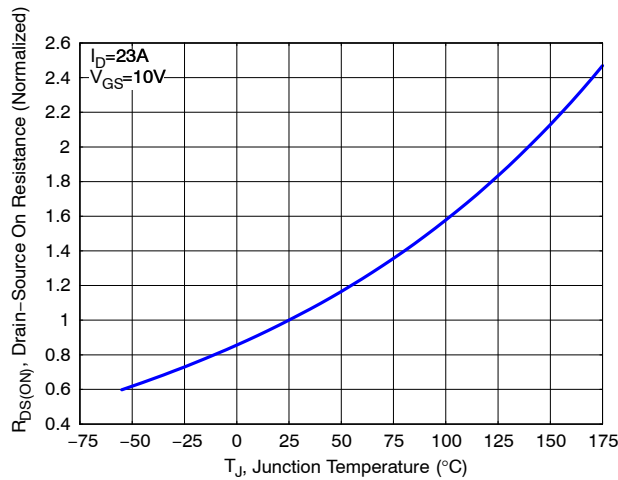


Figure 5. Normalized On-Resistance vs. Junction Temperature

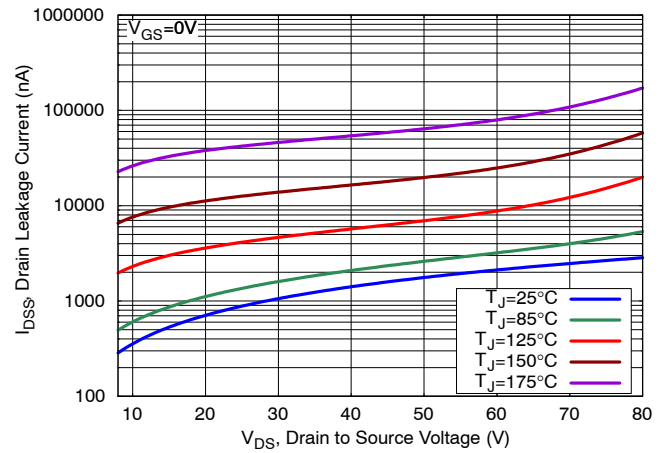


Figure 6. Drain Leakage Current vs. Drain Voltage

TYPICAL CHARACTERISTICS

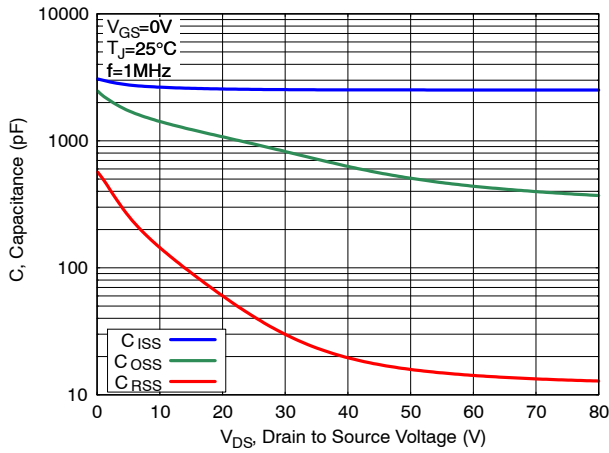


Figure 7. Capacitance Characteristics

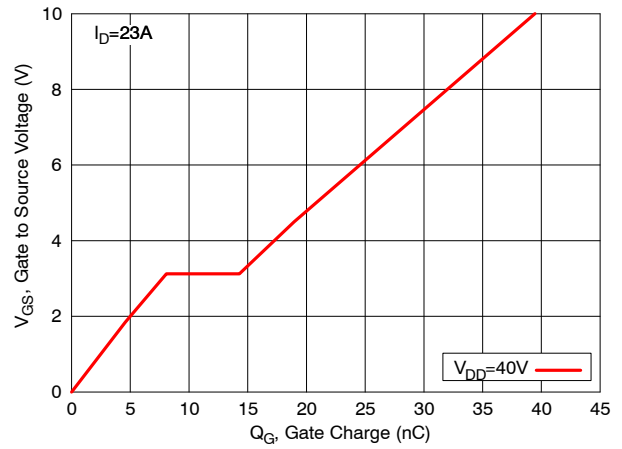


Figure 8. Gate Charge Characteristics

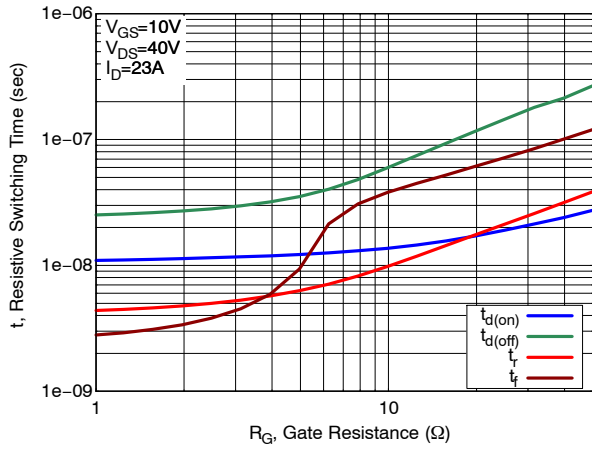


Figure 9. Resistive Switching Time Variation vs. Gate Resistance

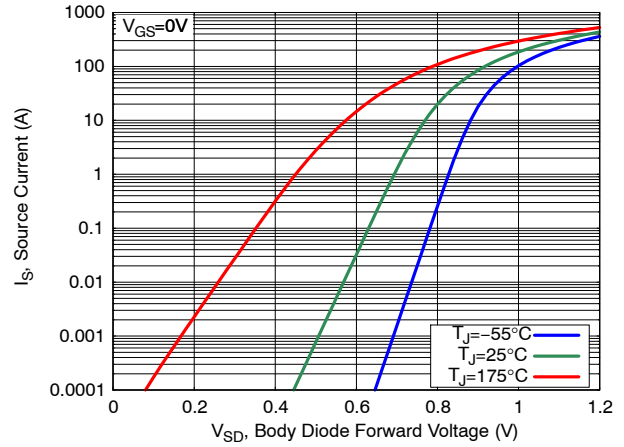


Figure 10. Diode Forward Characteristics

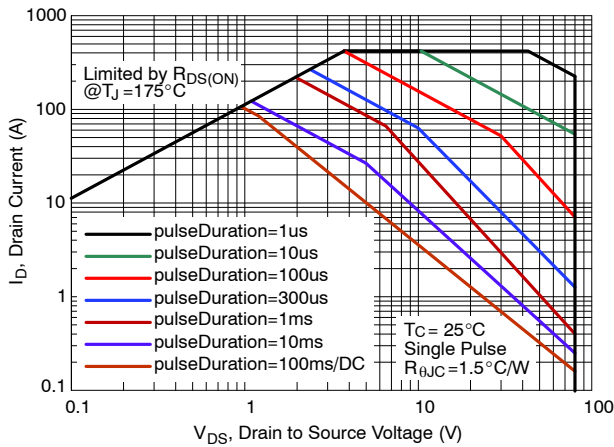


Figure 11. Safe Operating Area (SOA)

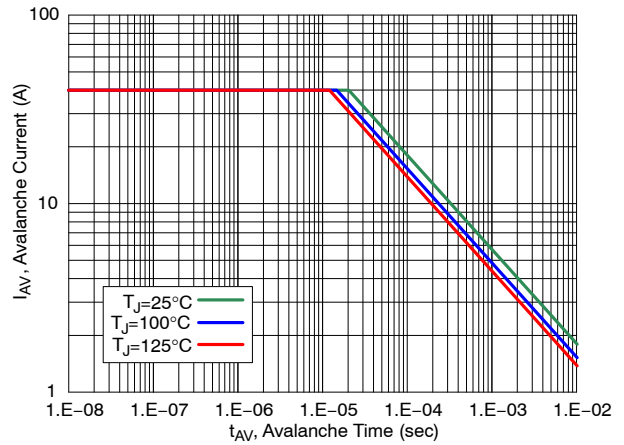


Figure 12. Avalanche Current vs. Pulse Time (UIS)

TYPICAL CHARACTERISTICS

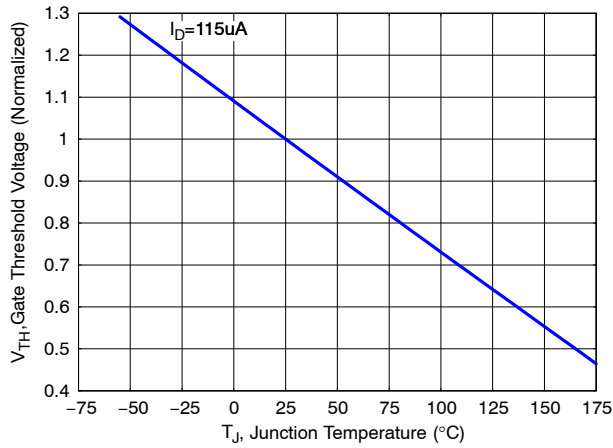


Figure 13. Gate Threshold Voltage vs. Junction Temperature

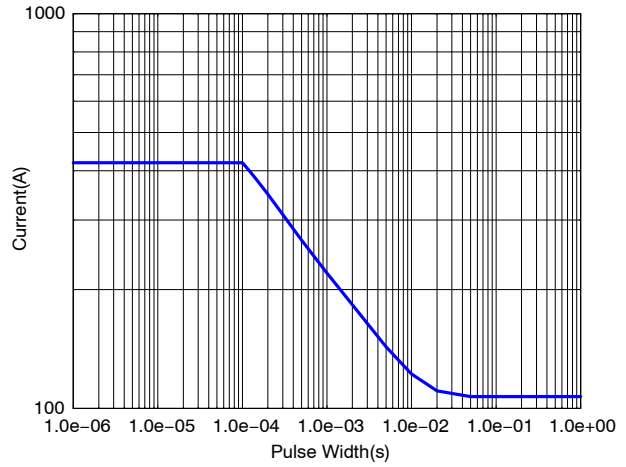


Figure 14. IDM vs. Pulse Width

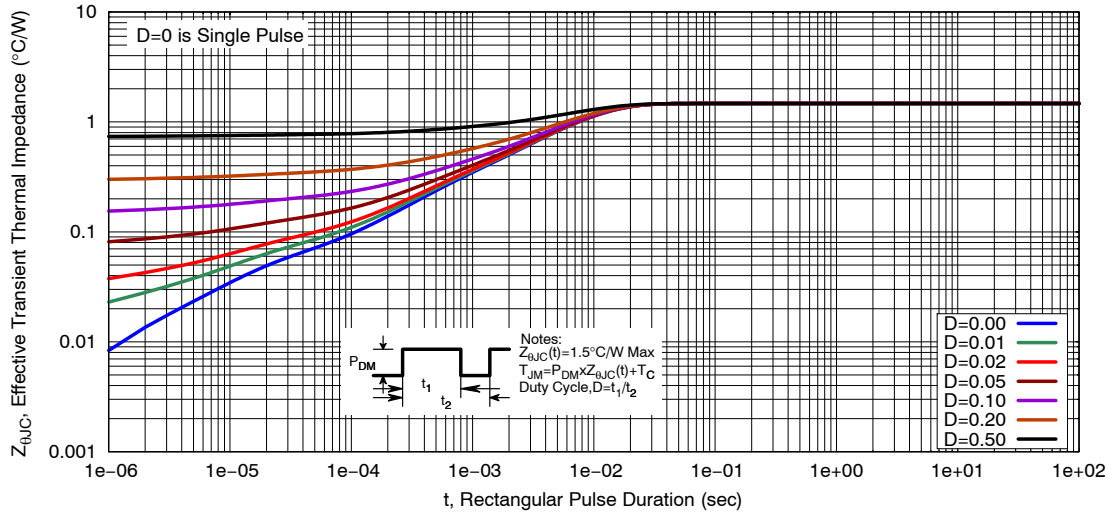
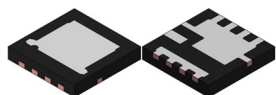


Figure 15. Transient Thermal Response

ORDERING INFORMATION

Device	Marking	Package	Shipping†
NTTFSSCH4D0N08XLTWG	4D0	WDFN9 (Pb-Free)	5000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

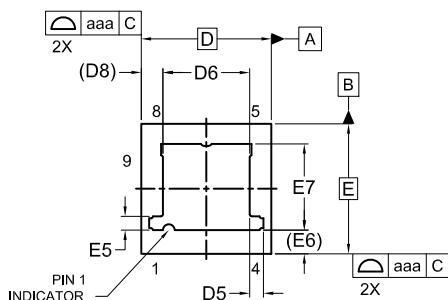


WDFN9 3.30x3.30x0.58, 0.65P

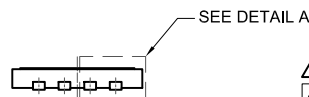
CASE 511BX

ISSUE B

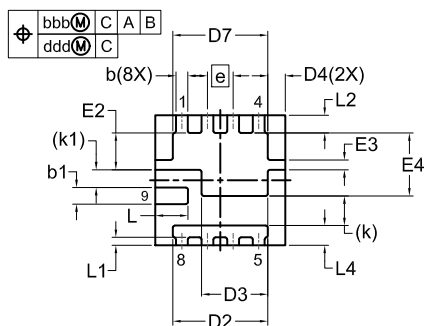
DATE 13 AUG 2024



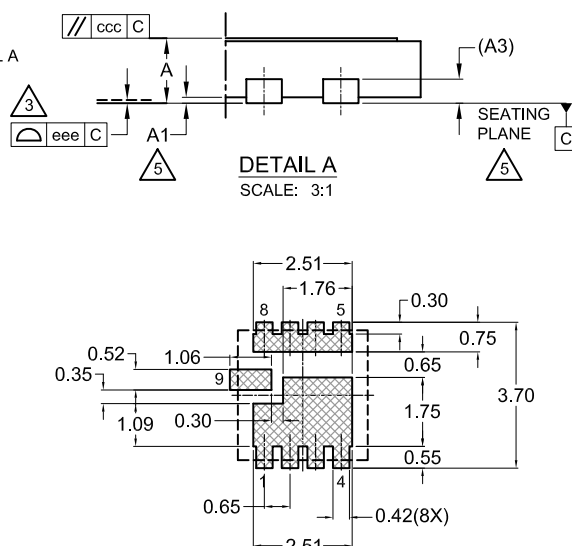
TOP VIEW



FRONT VIEW



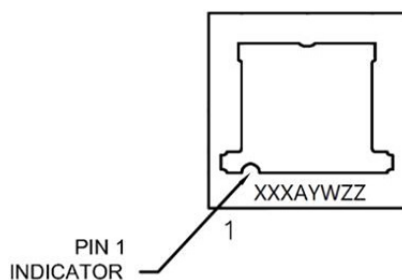
BOTTOM VIEW



LAND PATTERN RECOMMENDATION

*FOR ADDITIONAL INFORMATION ON OUR PB-FREE STRATEGY
AND SOLDERING DETAILS, PLEASE DOWNLOAD THE ONSEMI
SOLDERING AND MOUNTING TECHNIQUES REFERENCE
MANUAL. SOLDERRM/D.

GENERIC MARKING DIAGRAM*



XXX = Specific Device Code
A = Assembly Location
Y = Year
W = Work Week
ZZ = Assembly Lot Code

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present. Some products may not follow the Generic Marking.

UNIT IN MILLIMETERS			
DIM	MIN	NOM	MAX
A	0.53	0.58	0.63
A1	0.00	-	0.05
A3	0.20 REF		
b	0.25	0.30	0.35
b1	0.37	0.42	0.47
D	3.30 BSC		
D2	2.31	2.41	2.51
D3	1.58	1.68	1.78
D4	0.35	0.45	0.55
D5	0.25	0.35	0.45
D6	2.10	2.20	2.30
D7	2.31	2.41	2.51
D8	0.55 REF		
e	0.65 BSC		
E	3.30 BSC		
E2	0.84	0.94	1.04
E3	0.20	0.25	0.30
E4	1.50	1.60	1.70
E5	0.25	0.35	0.40
E6	0.60 REF		
E7	2.10	2.20	2.30
k	0.75 REF		
k1	0.45 REF		
L	0.73	0.83	0.93
L1	0.10	0.20	0.30
L2	0.35	0.45	0.55
L4	0.40	0.50	0.60
aaa	0.10		
bbb	0.10		
ccc	0.10		
ddd	0.05		
eee	0.08		

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DESCRIPTION:	WDFN9 3.30x3.30x0.58, 0.65P	PAGE 1 OF 1

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